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104-1002

(74)

• •

(54)

1 1 ()
2 2 ()
3
4 (TFT)
5a 5e 1 ()
6 (C/F)
7a 7d 2 ()
8 2 ()

< >

401 --- 1 402 ---
403 --- 404 ---
405, 410 --- / 406 ---
407 --- 408 ---
409 --- 601 --- 2
602 --- 603 ---
604 --- 605 ---
606 ---

가

1 () 2 ()
1 ()

TFT(Thin Film Transistor: TFT)

가 , TFT

BM(Black Matrix:BM), 2 ()

가 TFT(Thin Film Transistor: TFT) (on) , 1 (on) TFT 가

, 1 (101) 1 (gate) (102) (102) PECVD(Plasma Enhanced Chemical Vapor Deposition) (103)

, (phosphorus) (doping) (104a), (104b)

(source)/ (drain)(105,110) / (105,110)

, (106) , (106) ITO(Indium Titan Oxide) (pixel)(107)

, 2 2 () , 2 ()

2 , (201)

BM(Black Matrix: BM)(202)

, BM(202) (201)

(R)

, R 가

(G)

B , G 가 (203)

ITO(Indium Tin Oxide) (204)

1 () 2 ()

, 1 2

(108,205)

(108,205)

, 가 (anti-glare) , (anti-reflection)

3 (poly vinyl alcohol) 가 (iodic acid) (301) 가 2

(302a, 302b) (301) (304) ,
(303) .
1 () 2 ()
가 가 .
, 1 () 2 ()
가 가 .

가

ITO

ITO

ITO

ITO

가

가

4 (TFT) (401) () (402) ; (403), (404a), (404b), / (402) (405,410) (406) ; (407) (408) ; (408) ITO (409)

4

5a 5e 5a 1 ((gate)) (401) (402) 가 (S501).

3), 5b (404a), (404b), / (402) (405,410) (401) (406) (40) (S502). 가

(403) (402) PECVD(Plasma Enhanced Chemical Vapor Deposition) (404a) (phosphorus) (doping) (404b) (404a), (404b)

/ (404a), (404b) (source)/ (drain) 가

(S503). 5c (407) 가 (407)

5d (408) (407) (408) 가 (S504).
 (408) (poly vinyl alcohol)
 (408) 가 230 ~ 320
 가
 (408) ITO (409) ITO (409)
 9) 5e (408) ITO(Indium Titan Oxide) (pixel)(40
 가 (S505).
 6 (C/F)
 ;
 ; ITO
 6
 7a 7d 2 ()
 2 ()
 7a (601) (602)
 가 (S701). (601)
 (Black Matrix: BM)(602)
 7b (602) (R)
 가 (S702). BM(602)
 (R)
 가 (S703). (R) 가
 (G)
 (G) 가
 B)
 7c (604) 가
 (S704). (poly vinyl alcohol)
 (604)
 가 230 ~ 320
 가
 (604) ITO ITO
 7d (604) ITO (605)
 가 (S705). ITO(Indium Tin Oxide)

(605) .

8 2 ()
6) (603) (603) (604) (60

가 가 가

가 .

(57)

1. ;

/ ;
;
;

ITO .

2. ;

/
;
;

ITO

3. ;

;
;
;

ITO

4.

3

5.

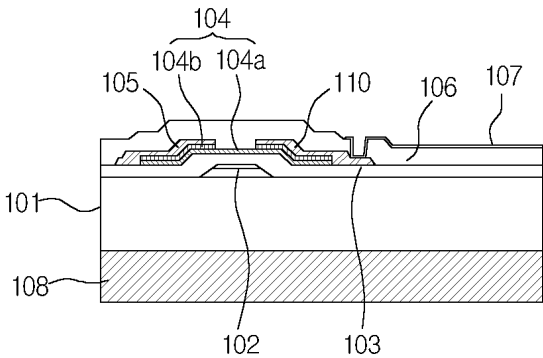
ITO

6.

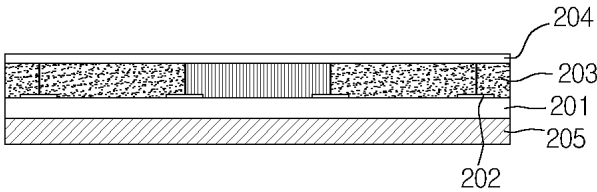
5

가

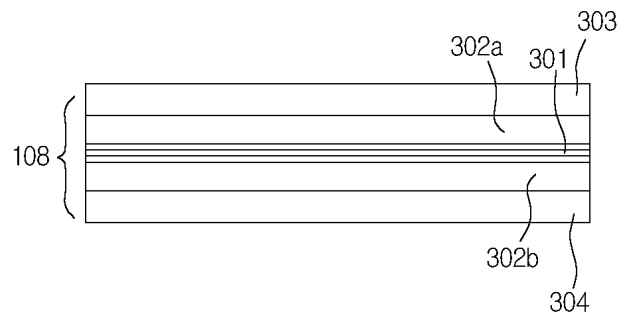
1



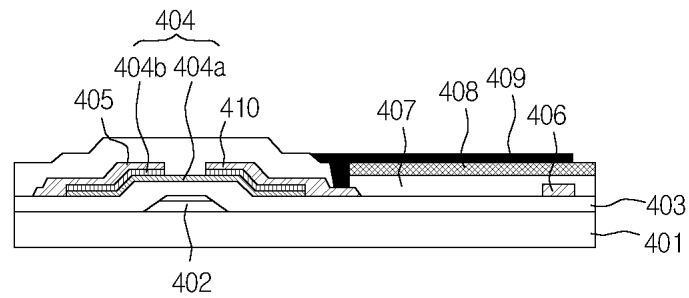
2



3



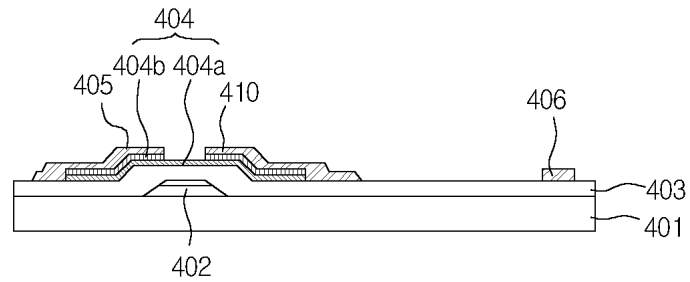
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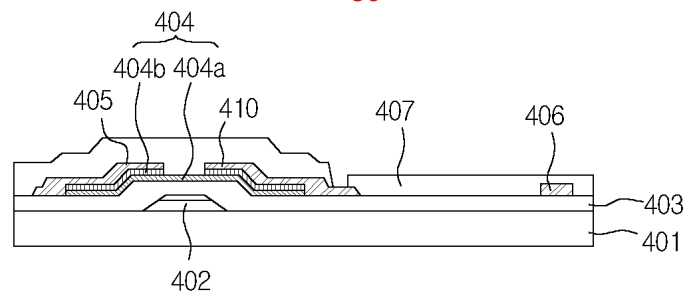
5a



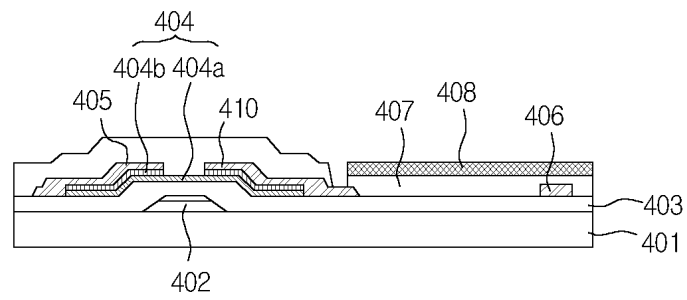
5b



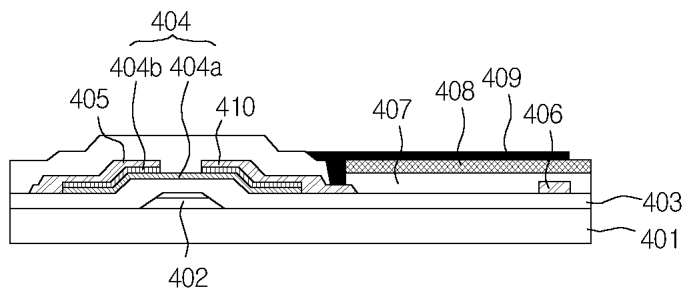
5c



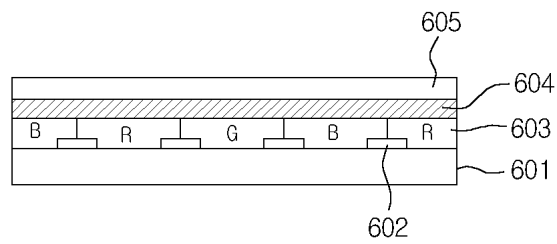
5d



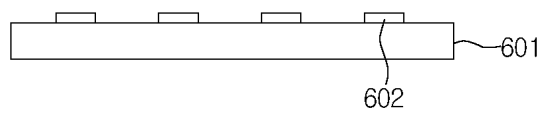
5e



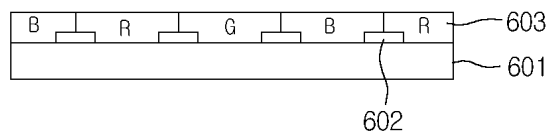
6



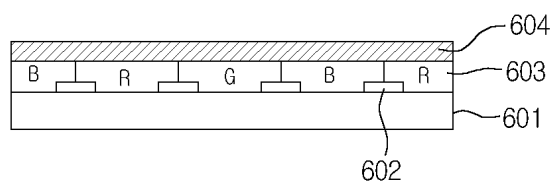
7a



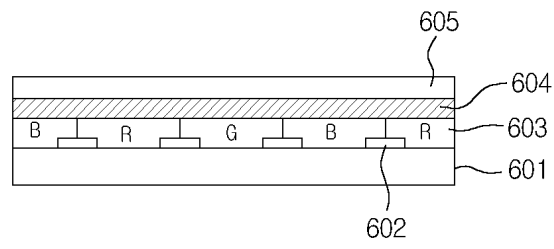
7b



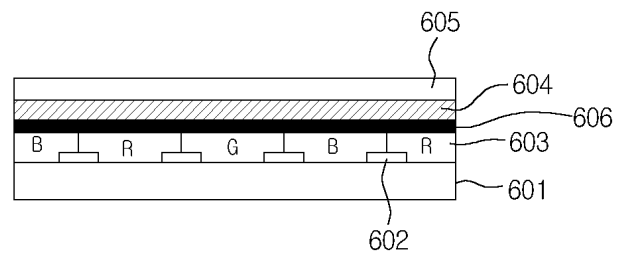
7c



7d



8



专利名称(译)	在基板中形成偏振膜的液晶显示装置及其制造方法		
公开(公告)号	KR1020040037943A	公开(公告)日	2004-05-08
申请号	KR1020020066786	申请日	2002-10-31
[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG显示器有限公司		
当前申请(专利权)人(译)	LG显示器有限公司		
[标]发明人	SA UNNYOUNG WOO JOUNGWON 우정원 LEE MANHOAN 이만환 HONG HYUNGKI 홍형기		
发明人	사언녕 우정원 이만환 홍형기		
IPC分类号	G02F1/1335 G02F1/136		
CPC分类号	G02F1/133528 G02F2001/133565		
外部链接	Espacenet		

摘要(译)

本发明公开了液晶显示装置及其制造方法，在内侧基板上形成偏振膜。其特征在于包括形成栅极总线和栅极电极的步骤，栅极金属膜被涂覆在根据本发明的内部基板中形成偏振膜的液晶显示装置的制造方法上，透明型绝缘板，形成基板的步骤，涂覆保护膜的步骤，用于器件钝化的结果，在保护膜上形成偏振膜的步骤，以及在偏振膜上形成ITO像素电极的步骤。关于步骤，依次形成栅极总线和栅极，栅极绝缘层，有源层，欧姆接触层，源/漏极和数据总线。液晶显示器形成偏振膜在根据本发明的内部基板上将偏振层沉积在滤色器基底材料和液晶显示器的薄膜晶体管基板中，并且可以形成厚度薄的液晶显示器。偏振膜，薄膜晶体管和滤色器。

